
AMENDMENTS TO THE CLAIMS

Please cancel claims 1-5 and 16-22 without prejudice or disclaimer of the underlying subject matter as set forth below:

1. (CANCELED).
2. (CANCELED).
3. (CANCELED).
4. (CANCELED).
5. (CANCELED).
6. (ORIGINAL) A semiconductor laser comprising:
a light emission function layer stack including a cladding layer and an active layer formed on one plane of a translucent substrate;
two electrodes having different polarities, which are provided on said light emission function layer stack side; and
a light leakage preventive film formed on the other plane of said translucent substrate.
7. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a light absorbing film.
8. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a light reflecting film.
9. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a dielectric film.
10. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a metal film.
11. (ORIGINAL) A semiconductor laser according to claim 6, wherein a thickness of said light leakage preventive film is set to a value of $\lambda/4n$ where λ is a

wavelength of light emitted from said light emission function layer stack and n is a refractive index of said light leakage preventive film.

12. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a multi-layer film of dielectrics, and a thickness of each layer of said multi-layer film of dielectrics is set to a value of $\lambda/4n$ where λ is a wavelength of light emitted from said light emission function layer stack and n is a refractive index of said light leakage preventive film.

13. (ORIGINAL) A semiconductor laser according to claim 6, wherein each layer of said light emission function layer stack is made from a GaN base semiconductor.

14. (ORIGINAL) A semiconductor laser according to claim 6, wherein said translucent substrate is made from sapphire.

15. (ORIGINAL) A semiconductor laser according to claim 6, wherein said translucent substrate is made from GaN.

16. (CANCELED).

17. (CANCELED).

18. (CANCELED).

19. (CANCELED).

20. (CANCELED).

21. (CANCELED).

22. (CANCELED).